

μPA675T

DESCRIPTION

The μPA675T is an N-channel vertical MOS FET. Because it can be driven by a voltage as low as 1.5 V and it is not necessary to consider a drive current, this FET is ideal as an actuator for low-current portable systems such as headphone stereos and video cameras.

FEATURES

- Two MOS FET circuits in package the same size as SC-70
- Automatic mounting supported
- Gate can be driven by a 1.5 V power source
- Because of its high input impedance, there's no need to consider a drive current
- Since bias resistance can be omitted, the number of components required can be reduced

ORDERING INFORMATION

PART NUMBER	PACKAGE
μPA675T ^{Note}	SC-88 (SSP)

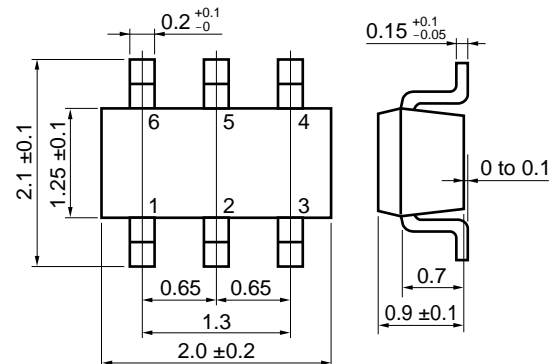
Note Marking: SA

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

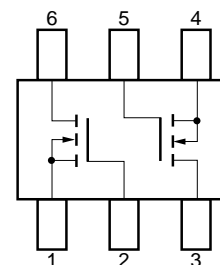
Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	16	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	±7.0	V
Drain Current (DC) (T _c = 25°C)	I _{D(DC)}	±0.1	A
Drain Current (pulse) ^{Note}	I _{D(pulse)}	±0.2	A
Total Power Dissipation (T _c = 25°C)	P _T	0.2	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Note PW ≤ 10 ms, Duty Cycle ≤ 50%

PACKAGE DRAWING (Unit: mm)



PIN CONNECTION



1. Source 1 (S1)
2. Gate 1 (G1)
3. Drain 2 (D2)
4. Source 2 (S2)
5. Gate 2 (G2)
6. Drain 1 (D1)

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ELECTRICAL CHARACTERISTICS (TA = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 16\text{ V}, V_{GS} = 0\text{ V}$			1.0	μA
Gate Leakage Current	I_{GSS}	$V_{GS} = \pm 7.0\text{ V}, V_{DS} = 0\text{ V}$			± 3.0	μA
Gate Cut-off Voltage	$V_{GS(off)}$	$V_{DS} = 3\text{ V}, I_D = 10\ \mu\text{A}$	0.5	0.8	1.1	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = 3\text{ V}, I_D = 10\text{ mA}$	20			mS
Drain to Source On-state Resistance	$R_{DS(on)1}$	$V_{GS} = 1.5\text{ V}, I_D = 1\text{ mA}$		20	50	Ω
	$R_{DS(on)2}$	$V_{GS} = 2.5\text{ V}, I_D = 10\text{ mA}$		7	15	Ω
	$R_{DS(on)3}$	$V_{GS} = 4.0\text{ V}, I_D = 10\text{ mA}$		5	12	Ω
Input Capacitance	C_{iss}	$V_{DS} = 3\text{ V}$		10		pF
Output Capacitance	C_{oss}	$V_{GS} = 0\text{ V}$		13		pF
Reverse Transfer Capacitance	C_{rss}	$f = 1\text{ MHz}$		3		pF
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 3\text{ V}, I_D = 10\text{ mA}$		15		ns
Rise Time	t_r	$V_{GS} = 3\text{ V}$		70		ns
Turn-off Delay Time	$t_{d(off)}$	$R_G = 10\ \Omega$		100		ns
Fall Time	t_f			110		ns

SWITCHING TIME MEASUREMENT CIRCUIT AND CONDITIONS

